

FAST HIGH VOLTAGE TRANSISTOR SWITCHES

The high-voltage switches of the model series HTS-SI and HTS-FI have been especially designed for scientific and industrial power pulse applications which require a fast and reproducible switching of peak currents at the kiloampere level. To achieve this, state-of-the-art power semiconductor devices, so-called IGBT's (Insulated Gate Bipolar Transistors) have been employed. These new switching elements of power electronics represent in principal a combination of the classical bipolar transistor with the modern vertical MOSFET. The advantages of both technologies; the current capability and low voltage drop of the bipolar transistor plus the high switching speed of the MOSFET, are ideally combined in the IGBT. By using a hundred or more interconnected IGBT's the switching modules of series HTS-SI/FI achieve the pulse power capability of gas discharge tubes and spark gaps. Additionally, IGBT switches offer advantages like simple connection, short recovery time, low jitter and last but not least the lifetime typical of semiconductor devices.

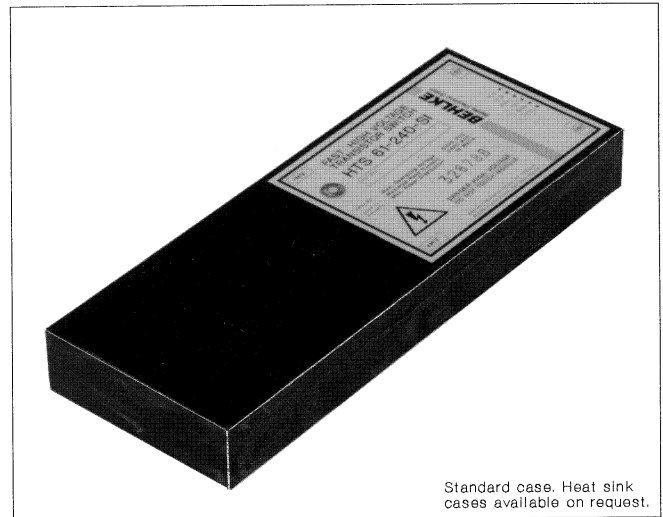
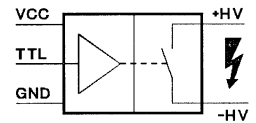
The turn-on rise times of BEHLKE IGBT switches are in practice mainly only limited by the circuit stray inductance. In contrast the turn-off rise times are determined by the bipolar characteristics of the IGBT's. Due to the recombination time of the minority carriers a relatively long turn-off-phase occurs. The turn-off-phase lasts approximately 5 μ s for the HTS-SI (- Standard IGBT) and approximately 1 μ s for the HTS-FI (- Fast IGBT) switch. The on-time corresponds to the control signal and can be varied between $t_{on(min)}$ and infinity. Being galvanically isolated, the devices can be used as high-side switches for positive as well as for negative voltages. The modules are protected against thermal overload, too high a signal frequency, unsuitable control signals, and incompatible auxiliary supplies. For reasons of reliability the devices are completely resin-encapsulated, but in case of failure, a cost-effective repair is possible at factory.

IMPORTANT!

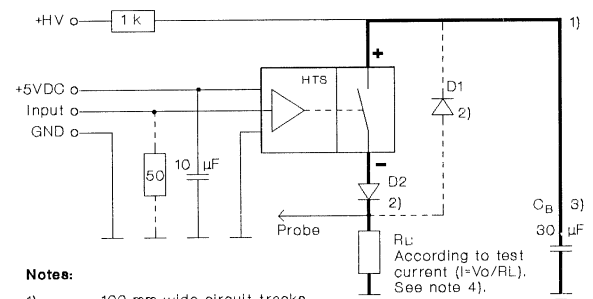
Do not exceed the rated reverse-blocking voltage, otherwise an undefined breakdown of the switch may occur. If the risk of a current reversal exists (caused by unclamped inductive loads or poor circuit layouts) the switch should be protected by an adequate external diode. For lowest stray inductances the switch should be contacted over the whole width of its terminal blocks. Mounting on a double-sided printed circuit board with 100 mm (4 inch) wide circuit tracks is recommended. In case of pulse transmission an impedance matching between switch, line and load has to be provided. For further design recommendations please refer to the general instructions.

HTS 61-240-SI 6 kV, 2.4 kA
HTS 61-160-FI 6 kV, 1.6 kA

- IGBT Technology
- High di/dt Capability
- Full Peak Current Turn-Off Capability

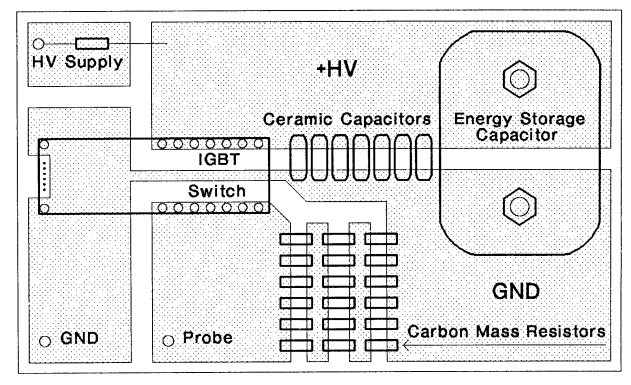


Test Circuit (High-Side Switch)



- Notes:**
- 1) 100 mm wide circuit tracks
 - 2) D1/D2 in case of current reversal only
 - 3) MAXWELL energy storage capacitor in parallel with 500 nF ceramic cap.
 - 4) ALLEN BRADLEY 2 watt mass resistors, > 30 pieces in parallel & series. RL is 2.5 Ohm (-SI) respectively 3.6 Ohm (-FI) for $I_p(max)$ at $V_o(max)$.

Test Board (Top View)



TECHNICAL DATA

SPECIFICATION	SYMBOL	CONDITION / COMMENT	61-240-SI	61-160-FI	UNIT
Maximum Operating Voltage	$V_{O(max)}$	$T_{case} = 25^{\circ}C$	± 6000		VDC
Minimum Operating Voltage	$V_{O(min)}$	Recommended for saturated switching	600		VDC
Breakdown Voltage	V_{br}	$I_{off} > 10 \text{ mA}$, $T_{case} = 25^{\circ}C$	6600		VDC
Temperature Coefficient of V_{br}			+9.0	+7.56	V/°C
Max. Reverse Blocking Voltage	V_{rb}		180		VDC
Isolation Voltage	V_I	Continuously	10000		VDC
Typical Saturation Voltage	V_{sat}	$0.1 \times I_{P(max)}$, $0.8 \times V_O$, $T_{case} = 25^{\circ}C$	18	27	VDC
		$1.0 \times I_{P(max)}$, $0.8 \times V_O$, $T_{case} = 25^{\circ}C$	120	84	
Maximum Peak Current 1)	$I_{P(max)}$	$t_p < 100 \mu s$, duty cycle $< 1\%$, $T_{case} = 25^{\circ}C$	2400	1600	ADC
		$t_p < 1 \text{ ms}$, duty cycle $< 1\%$, $T_{case} = 25^{\circ}C$	1500	1000	
		$t_p < 100 \mu s$, duty cycle 50%, $T_{case} = 25^{\circ}C$	825	550	
		$t_p < 1 \text{ s}$, duty cycle 50%, $T_{case} = 25^{\circ}C$	600	400	
Maximum Continuous Current	I_L	Standard plastic case, $T_{case} = 25^{\circ}C$	3	2	ADC
Maximum Off-State Current	I_{off}	$0.8 \times V_O$, $T_{case} = 25^{\circ}C$	1		mADC
Minimum On-Time	$t_{on(min)}$		1	0.2	μs
Turn-On Delay Time	$t_{d(on)}$	$0.1 \times I_{P(max)}$	130		ns
Typical Turn-On Rise Time	$t_{r(on)}$	$0.1 \times I_{P(max)}$, $0.8 \times V_O$	50	30	ns
		$1.0 \times I_{P(max)}$, $0.8 \times V_O$	130	90	
Typical Turn-Off Rise Time 2)	$t_{r(off)}$	Resistive load	5	0.8	μs
Typical Turn-On Jitter	$t_{j(on)}$	$V_{tr} = 5VDC$, $V_{aux} = 5.00 \text{ VDC}$	500		ps
Maximum Burst Frequency 1)	$f_{b(max)}$	(1 / Minimum Pulse Spacing)	0.25	1	MHz
Max. Number of Pulses/Burst 1)	N_B	Use burst option for > 20 pulses / $100\mu s$	20		
Max. Continuous Frequency 1)	$f_{c(max)}$		1	6	kHZ
Max. Cont. Power Dissipation	$P_{d(max)}$	Increased $P_{d(max)}$ on request	25		Watts
Linear Temp. Derating of $P_{d(max)}$		$T_{case} > 25^{\circ}C$	0.55		W/°C
Temperature Range	T_O	Extended temperature range on request	-30... +70		°C
Switch Natural Capacitance	C_N	Capacitance between switch poles	350	210	pF
Coupling Capacitance	C_C	Between power and control part	30		pF
Auxiliary Supply Voltage	V_{aux}	Maximum tolerance $\pm 5\%$	5		VDC
Auxiliary Supply Current	I_{aux}	@ $f_{c(max)}$	400		mADC
Control Voltage	V_{tr}	$> 3VDC$ recommended	2-10		VDC
Fault Detection Signal		"Low" in case of fault	High: 4.8 (Typ.)	Low: 0.2	VDC
Dimensions		Case only	199.5 x 76.4 x 25.4		mm ³
Weight			750		g

- 1) CAUTION: These data have to be considered in conjunction with the maximum continuous power dissipation! Please refer to the general instructions.
 2) Faster turn-off rise times are optionally available at reduced peak current capability. Please consult factory.

